

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5051-448CT		Serial No.: To Be Assigned	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Kevin J. Linthicum, et al.			
				Filing Date: Concurrently Herewith		GAU:	
U.S. PATENT DOCUMENTS							
Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
<i>GM</i>	1	Re. 34,861	02/14/95	Davis et al.	437	100	
	2	6,153,010	11/28/00	Koyoku et al.	117	95	
	3	6,100,111	08/08/00	Konstantinov	438	92	
	4	6,100,104	08/08/00	Haerle	438	33	
	5	<u>6,051,849</u>	04/08/00	Davis	257	103	<i>Do not consider</i>
	6	6,051,849	04/08/00	Davis	257	103	
	7	5,915,194	06/22/99	Powell et al.	438	478	
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	36	EP 0 942 459 A1	09/15/99	EPO			
	37	11-145516	05/28/99	Japan			X (Abstract)
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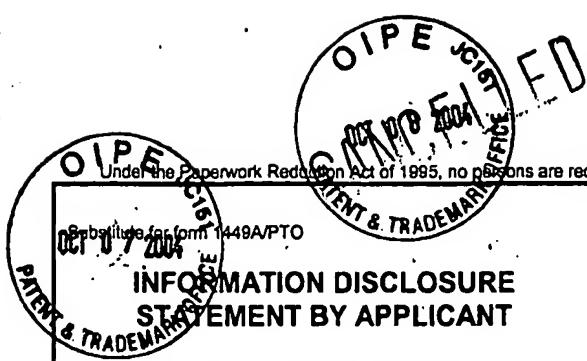
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete If Known

Application Number	10/633,952
Filing Date	August 4, 2003
First Named Inventor	Linthicum, Kevin J.
Art Unit	2815
Examiner Name	Jerome Jackson, Jr.
Attorney Docket Number	013921-000025

U.S. PATENT DOCUMENTS

U.S. PATENT DOCUMENTS					
Examiner Initials'	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
GJ	AA	5,633,192	05-27-97	Moustakas et al.	
	AB	5,686,738	11-11-97	Moustakas	
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NON PATENT LITERATURE DOCUMENTS

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